

**Amendments to the Claims**

Please cancel Claim 1. Please add new Claim 2. The Claim Listing below will replace all prior versions of the claims in the application:

**Claim Listing**

1. (Canceled)
2. (New) A method of selecting a word line in a dynamic random access memory to store a voltage level in a memory cell comprising:
  - coupling a controlled high supply voltage level that is greater than the voltage level stored in the memory cell to a level shifter circuit, the level shifter circuit comprising a pair of cross-coupled transistors connected drain-to-gate and having respective sources coupled to the controlled high supply voltage;
  - coupling a logic signal having only logic levels that are less than the controlled high supply voltage level to the level shifter circuit to produce a control signal having a logic state at the controlled high supply voltage level; and
  - driving a selected word line to the controlled high supply voltage level in response to the control signal.